

METHOD AND ARRAY FOR PROCESSING CARRIER MATERIALS BY MEANS OF HEAVY ION RADIATION AND SUBSEQUENT ETCHING

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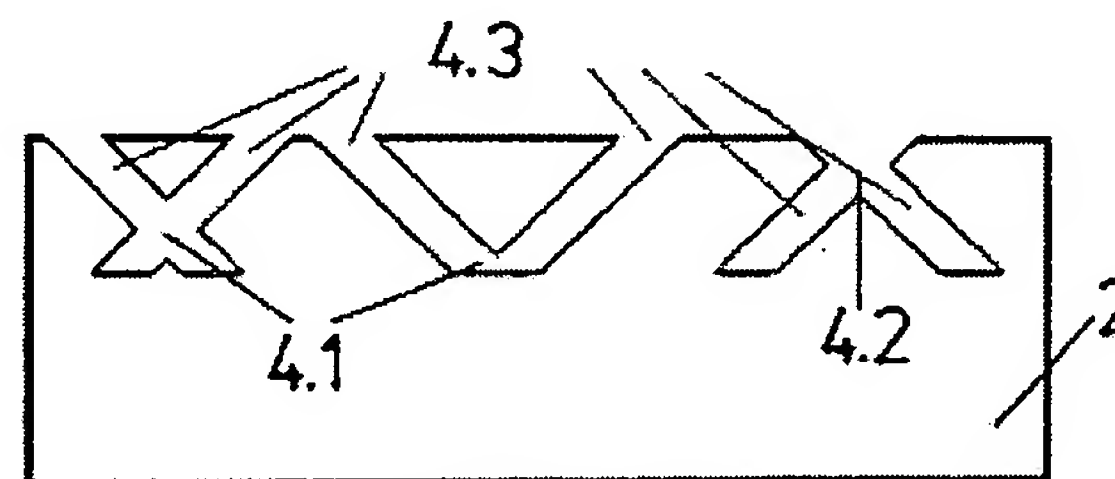
Cited documents:

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Abstract of WO2004015161

The invention relates to a method and an array for processing carrier materials by means of heavy ion radiation and subsequent etching, wherein the heavy ion radiation is carried out in such a way that a ray beam (1) of an energy-rich heavy ion radiation (1.1) incides on the surface (2) of a carrier material in at least two different angles. According to the invention, the fluence, the energy and the direction of incidence of the heavy ion rays (1.1) are selected in such a way that a maximum amount of intersecting or coinciding latent ion traces (3) and common numbers of incisions of the recesses (4) resulting from a chemical etching process following heavy ion radiation are obtained.



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